Silicon Pin diode

# 2 Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode		
2	anode	1 2	<b>├</b>
		Top view	

# 3 Ordering information

**Table 2. Ordering information** 

Type number	Package	Package				
	Name	Description	Version			
BAP65-03	-	plastic surface-mounted package; 2 leads	SOD323			

# 4 Marking

Table 3. Marking

Type number	Marking code
BAP65-03	D3 <sup>[1]</sup>

<sup>[1]</sup> The marking bar indicates the cathode (see simplified outline graphic in  $\underline{\text{Table 1}}$ )

# 5 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	continuous reverse voltage		-	30	V
l <sub>F</sub>	continuous forward current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 90 °C	-	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

## 6 Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		120	K/W

BAP65-03

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## 7 Characteristics

## **Table 6. Characteristics**

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
/ <sub>F</sub>	forward voltage	$I_F = 50 \text{ mA}$	-	0.9	1.1	V	
R	reverse current	V <sub>R</sub> = 20 V		-	20	nA	
$C_d$	diode capacitance	f = 1 MHz (see <u>Figure 1</u> )	·				
		V <sub>R</sub> = 0 V	-	0.65	-	pF	
		V <sub>R</sub> = 1 V	-	0.55	0.9	pF	
		V <sub>R</sub> = 3 V	-	0.5	0.8	pF	
		V <sub>R</sub> = 20 V	-	0.375	-	pF	
D	diode forward resistance	f = 100 MHz (see Figure 2)					
		I <sub>F</sub> = 1 mA	-	1	-	Ω	
		I <sub>F</sub> = 5 mA	[1] _	0.65	0.95	Ω	
		I <sub>F</sub> = 10 mA	[1] _	0.56	0.9	Ω	
		I <sub>F</sub> = 100 mA	-	0.35	-	Ω	
SL	isolation	V <sub>R</sub> = 0 V (see <u>Figure 4</u> )					
		f = 900 MHz	-	10.2	-	dB	
		f = 1800 MHz	-	5.8	-	dB	
		f = 2450 MHz	-	4.1	-	dB	
L <sub>ins</sub>	insertion loss	See Figure 3.					
		I <sub>F</sub> = 1 mA					
		f = 900 MHz	-	0.11	-	dB	
		f = 1800 MHz	-	0.14	-	dB	
		f = 2450 MHz	-	0.18	-	dB	
		I <sub>F</sub> = 5 mA					
		f = 900 MHz	-	0.06	-	dB	
		f = 1800 MHz	-	0.10	-	dB	
		f = 2450 MHz	-	0.14	-	dB	
		I <sub>F</sub> = 10 mA					
		f = 900 MHz	-	0.06	-	dB	
		f = 1800 MHz	-	0.1	-	dB	
		f = 2450 MHz	-	0.13	-	dB	
-ins	insertion loss	I <sub>F</sub> = 100 mA			1		
		f = 900 MHz	-	0.05	-	dB	
		f = 1800 MHz	-	0.1	-	dB	
		f = 2450 MHz	_	0.14	-	dB	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
τL	charge carrier life time	when switched from $I_F$ = 10 mA to $I_R$ = 6 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 3 mA	-	0.17	-	μs
L <sub>S</sub>	series inductance	I <sub>F</sub> = 100 mA; f = 100 MHz	-	1.5	-	nH

<sup>[1]</sup> Guaranteed on AQL basis; inspection level S4, AQL 1.0

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## 8 Graphical data

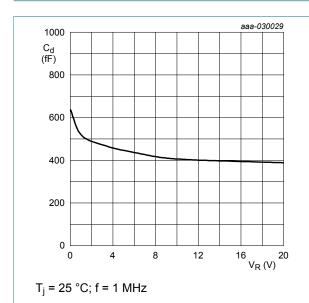


Figure 1. Diode capacitance as a function of reverse voltage (typical values)

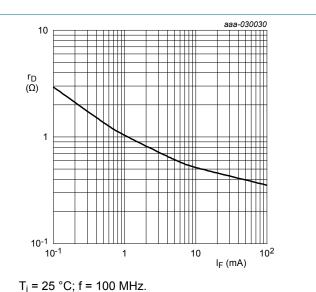
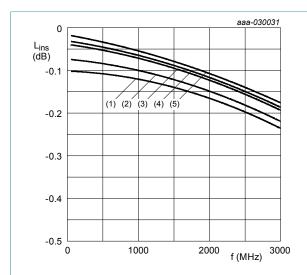


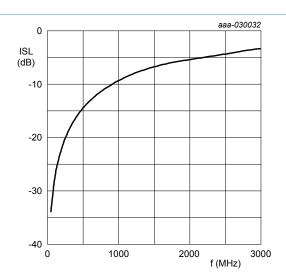
Figure 2. Diode forward resistance as a function of forward current (typical values)



Diode inserted in series with a 50  $\Omega$  strip line circuit and biased via the analyzer T-network. T<sub>amb</sub> = 25 °C.

- (1)  $I_F = 0.5 \text{ mA}$
- (2)  $I_F = 1 \text{ mA}$
- (3)  $I_F = 5 \text{ mA}$
- (4)  $I_F = 10 \text{ mA}$
- (5)  $I_F = 100 \text{ mA}$

Figure 3. Insertion loss of the diode in on-state as a function of frequency (typical values)



Diode zero-biased and inserted in series with a 50  $\Omega$  strip line circuit.  $T_{amb}$  = 25  $^{\circ}C.$ 

Figure 4. Isolation of the diode in off-state as a function of frequency (typical values)

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# 9 Package outline

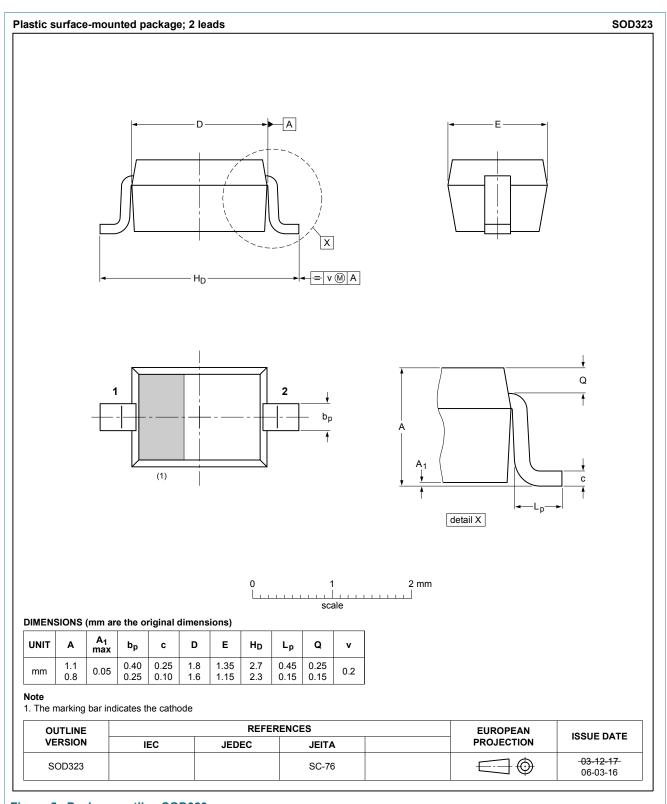


Figure 5. Package outline SOD323

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# 10 Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BAP65-03 v.5.2	20190128	Product data sheet	-	BAP65-03 v.5.1		
Modifications:	Changed title	to Silicon PIN diode				
BAP65-03 v.5.1	20181211	Product data sheet	-	BAP65-03 v.5		
Modifications:		<ul> <li>changed Typ value off L<sub>ins</sub> at 2450 MHz to 0.18 dB</li> <li>Changed condition I<sub>F</sub> on L<sub>S</sub>from 10 mA to 100 mA</li> </ul>				
BAP65-03 v.5	20180802	Product data sheet	-	BAP65-03 v.4		
Modifications:		<ul> <li><u>Section 1.2</u> "Features and benefits" has been updated.</li> <li>The "Legal information" pages have been updated.</li> </ul>				
BAP65-03 v.4	20040211	Product data sheet	-	BAP65-03 v.3		

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## 11 Legal information

#### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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